36-40GHz Low Noise Amplifier

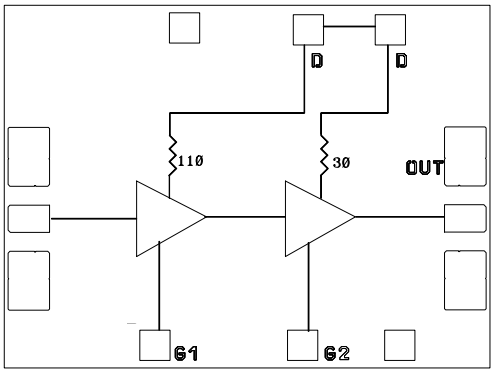
GaAs Monolithic Microwave IC

Description

The CHA2091 is a two-stage wide band monolithic low noise amplifier.

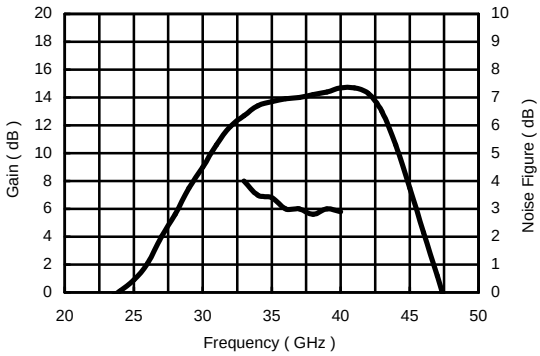
The circuit is manufactured with a standard HEMT process: 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography.

It is supplied in chip form.



Main Features

- Broad band performance 36-40GHz
- 2.5dB noise figure, 36-40GHz
- 14dB gain, ± 0.5dB gain flatness
- Low DC power consumption, 45mA
- 20dBm 3rd order intercept point
- Chip size: 1,67 x 1,03 x 0.1mm



On wafer typical measurements.

Main Characteristics

Tamb = +25°C

Symbol	Parameter	Min	Typ	Max	Unit
NF	Noise figure, 36-40GHz		2.5	4.0	dB
G	Gain	12	14		dB
ΔG	Gain flatness		± 0.5	± 1.0	dB

ESD Protections : Electrostatic discharge sensitive device observe handling precautions !

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Electrical Characteristics

Tamb = +25℃,
Bias Conditions: Vd = +4V Id=45mA

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	36		40	Ghz
G	Gain (1)	12	14		dB
ΔG	Gain flatness (1)		± 0.5	± 1.0	dB
NF	Noise figure (1)		2.5	3.5	dB
VSWRin	Input VSWR (1)			3.0:1	
VSWRout	Ouput VSWR (1)			3.0:1	
IP3	3rd order intercept point		20		dBm
P1dB	Output power at 1dB gain compression		12		dBm
Id	Drain bias current		45		mA

(1) These values are representative of on-wafer measurements that are made without bonding wires at the RF ports.When the chip is attached with typical 0.15nH input and output bonding wires, the indicated parameters should be improved.

Absolute Maximum Ratings (1)

Tamb = +25℃

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	4.0	V
Pin	Maximum peak input power overdrive (2)	+15	dBm
Top	Operating temperature range	-40 to +85	℃
Tstg	Storage temperature range	-55 to +125	℃

(1) Operation of this device above anyone of these parameters may cause permanent damage.
(2) Duration < 1s.

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Typical Results

Chip Typical Response (On wafer Sij) :

Tamb = +25℃
Bias conditions: Vd = +4V, Id=45mA

Freq GHz	S11 dB	S11 °	S12 dB	S12 °	S21 dB	S21 °	S22 dB	S22 °
10	-6	170.2	-57.3	-141	-12.4	11.3	-5.68	177.7
12	-7.1	156.5	-54.1	-157	-9.98	-12.7	-6.93	152.9
14	-8.42	145.2	-50.3	173.7	-8.72	-32.7	-8.54	131.2
16	-10	137	-48.1	158	-6.92	-51.3	-9.44	113
18	-11.5	132.1	-49.6	138.4	-5.05	-71.3	-11.3	93
20	-13	129	-47.8	120.7	-3.74	-93.7	-14.2	81.8
21	-13.6	127.7	-48.2	107	-3.31	-101	-15.1	80.4
22	-14.2	126.6	-49.1	114.5	-2.37	-107	-15.8	75.6
23	-14.8	122.7	-50.1	130.8	-0.72	-117	-17.5	61.4
24	-16.1	116.3	-45.5	130.2	0.08	-130	-23.2	51.5
25	-18.2	111	-42.9	121.1	0.86	-138	-32.6	132.7
26	-21.8	108.1	-42.2	109.7	2.11	-146	-21.7	167.7
27	-30	127.3	-40.8	107	3.95	-156	-16.2	165.6
28	-26.2	-140	-39.6	104.3	5.61	-169	-12.9	151.8
29	-18.5	-136	-36.8	93	7.52	176	-11	140.8
30	-14.5	-146	-34.8	85	8.99	157.9	-9.98	128.3
31	-12.3	-159	-32.5	68.7	10.58	139.4	-8.78	121.3
32	-10.9	-173	-31.8	48.3	11.88	117.3	-7.48	109.9
33	-10.5	174.9	-30.8	28.7	12.69	94.8	-6.88	95.3
34	-10.5	165.2	-29.8	7.3	13.36	72.8	-6.94	82.8
35	-11.1	156.1	-29.6	-15.2	13.72	50.2	-7.25	70.8
36	**-11.3**	**150.5**	**-29.5**	**-33.9**	**13.93**	**28.2**	**-7.94**	**60.9**
37	**-11.6**	**144**	**-30.1**	**-55.6**	**13.99**	**6.7**	**-8.73**	**52.2**
38	**-12**	**133**	**-29.6**	**-69.8**	**14.2**	**-14.5**	**-9.57**	**47.1**
39	**-12.9**	**115.4**	**-28.7**	**-85.8**	**14.39**	**-37.1**	**-10.2**	**43.7**
40	**-14.7**	**87.2**	**-29**	**-120**	**14.65**	**-61.2**	**-9.88**	**40.4**
41	-15.5	25.3	-28.1	-144	14.71	-88.7	-9.19	30.1
42	-10.7	-42.3	-27.8	-176	14.34	-121	-8.66	10.8
43	-6.09	-86.6	-28.3	146.7	12.98	-154	-8.99	-16.9
44	-3.4	-119	-30.4	111.9	10.59	174.3	-10.5	-50
45	-2.22	-143	-32.9	90	7.53	147.6	-12.2	-83.8
46	-1.59	-160	-35.2	62.9	4.31	125.2	-13	-119
47	-1.15	-175	-35.3	39	1.21	105.5	-12.5	-149
48	-0.84	173.2	-43.5	-26.6	-2.06	88.2	-11.8	-174
49	-0.85	163.7	-39.4	27.3	-5.61	72.6	-10.8	169
50	-0.67	154.7	-36.9	31.8	-9.07	58.2	-10.1	156.4

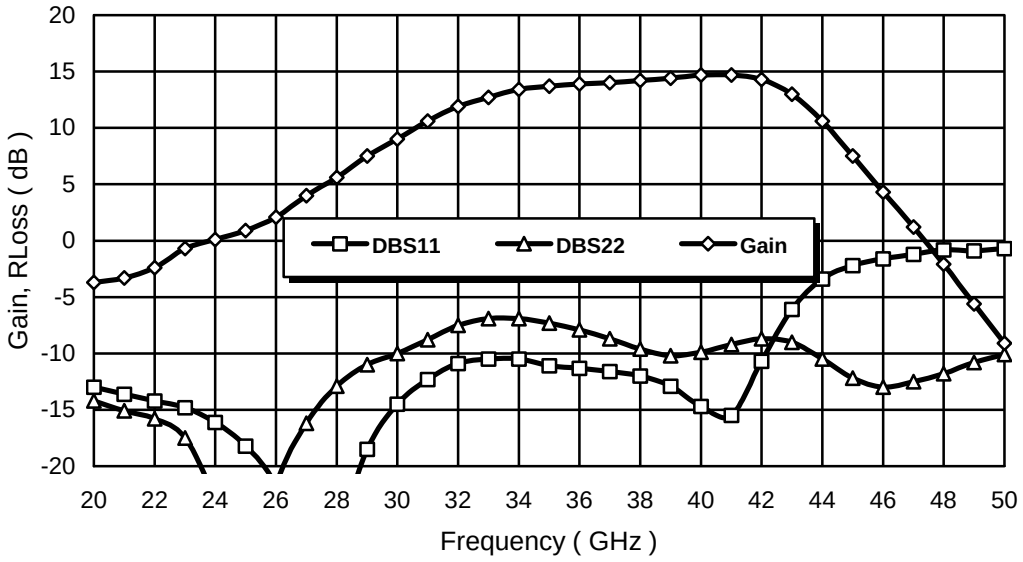
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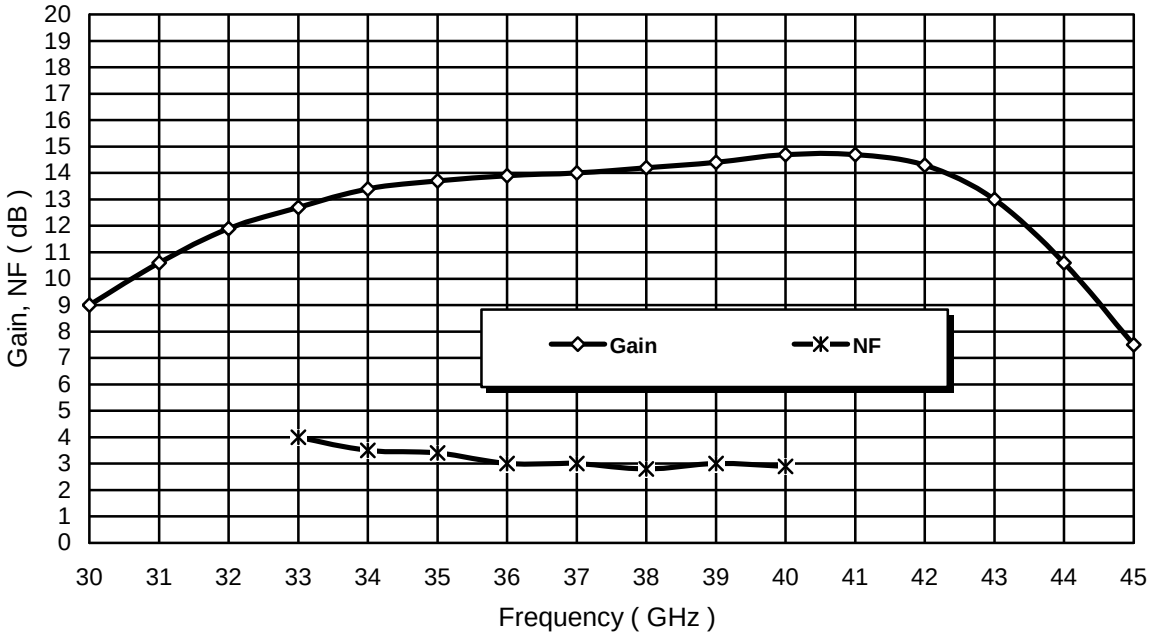
Typical Results

Chip Typical Response (On wafer Sij) :

Tamb = +25℃
Vd = +4V Id=45mA



Typical Gain and Matching measurements on wafer



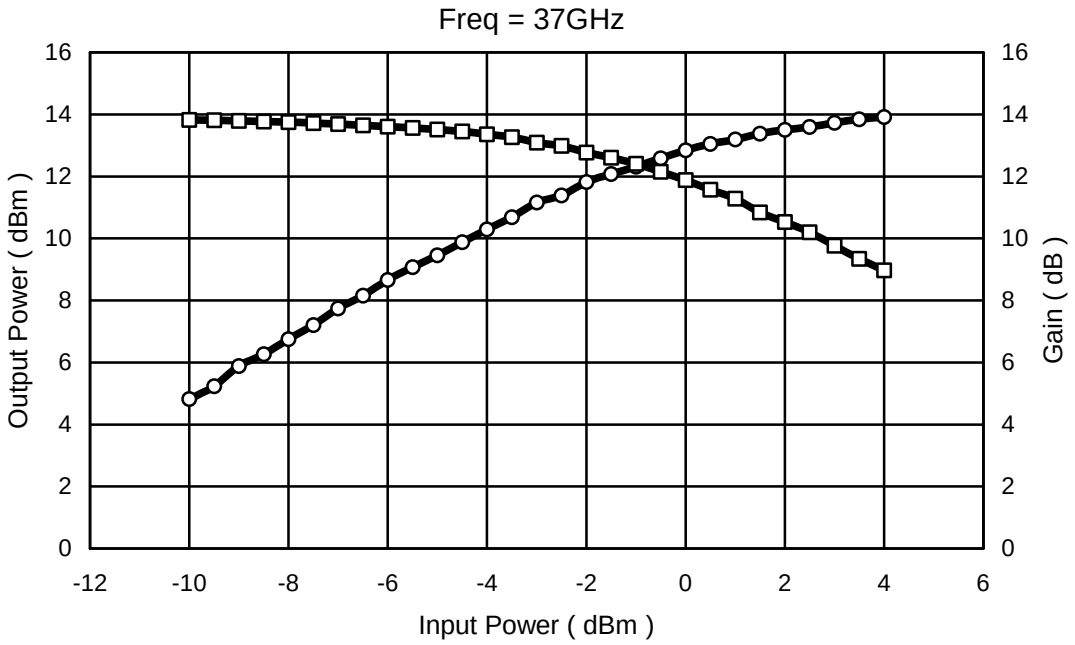
Typical Gain and Noise Figure measurements on wafer

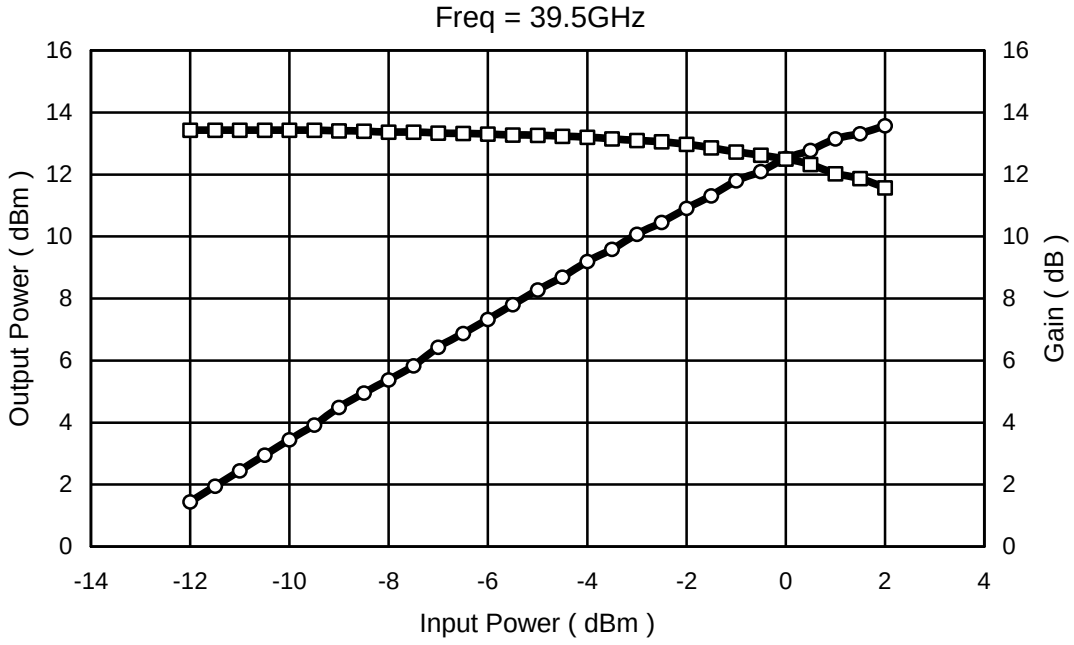
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Typical Results

Tamb = +25°C
Vd = +4V ; Id = 45mA



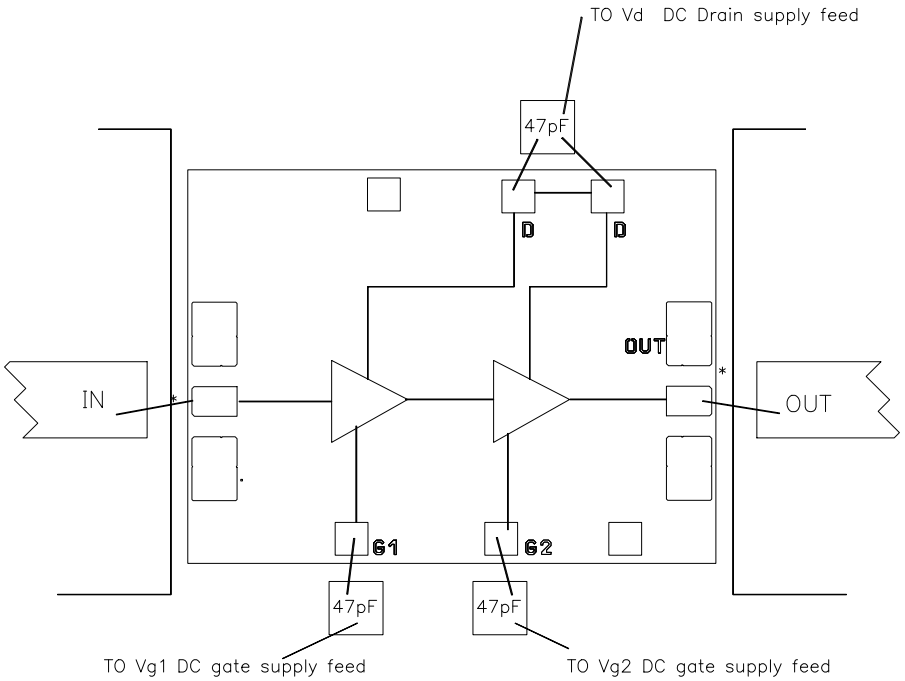


Typical Output Power and Gain measurements in test jig
(included losses of the jig)

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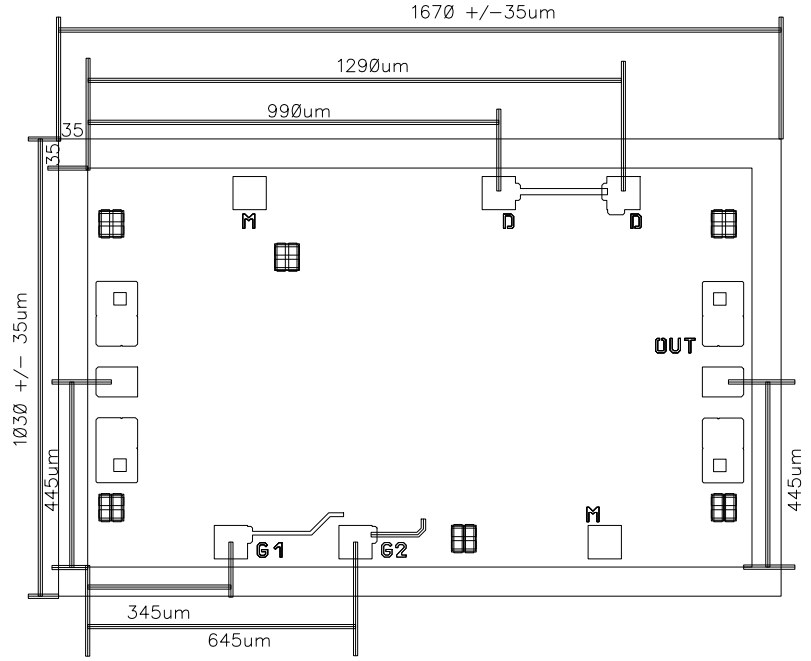
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Typical Chip Assembly



- Nominal Input and Output bonding :0.3nH for one 25um bond wire.
- Chip backside is DC and RF bonding grounded

Mechanical data



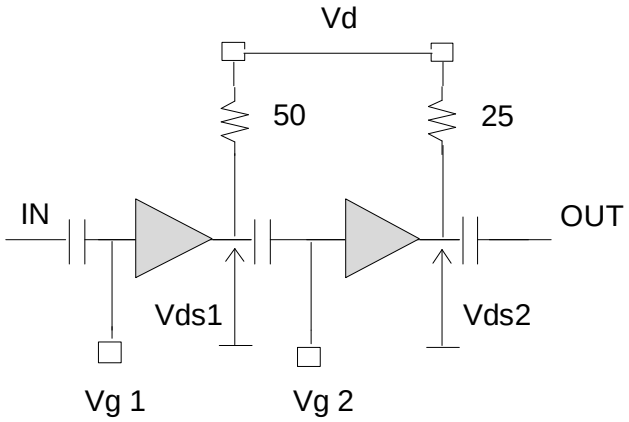
Pad size : 80/80um, chip thickness 100um

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Chip Biasing

This chip is a two stage amplifier, and flexibility is provided by the access to number of pads. The internal DC electrical schematic is given in order to use these pads in a safe way.



The two requirements are :

N°1 : Not exceed Vds = 3.5Volt (internal Drain to Source voltage).
N°2 : Not biased in such a way that Vgs becomes pos itive.
(internal Gate to Source voltage)

We propose two standard biasing :

Low Noise and low consumption : Vd = 3.5V and Id = 30mA.

Low Noise and high output power : Vd = 4.0V and Id = 45mA.(A separate acces to the gate voltages of the first and the output stage is provided. Nominal bias is obtained for a typical current of 30mA for the output stage and 15 mA for the first stage. The first step to bias the amplifier is to tune the Vg1 =-1V and Vg2 to drive 30mA for the full amplifier. Then Vg1 is reduced to obtain 45 mA of current through the amplifier.

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Ordering Information

Chip form : CHA2091-99F/00

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